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Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	11
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	512 x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 4x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	14-TSSOP (0.173", 4.40mm Width)
Supplier Device Package	14-TSSOP
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l021d4p6

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Description STM32L021x4

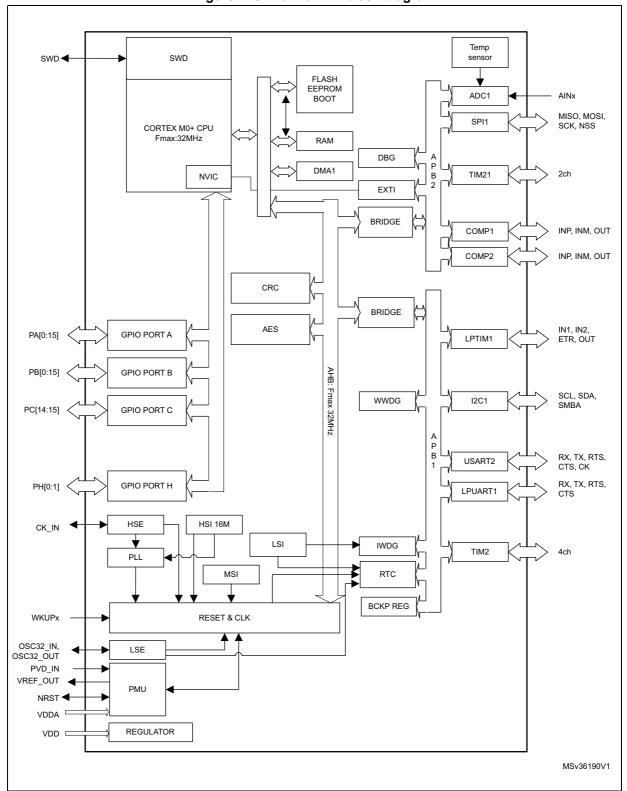


Figure 1. STM32L021x4 block diagram



Functional overview STM32L021x4

3 Functional overview

3.1 Low-power modes

The ultra-low-power STM32L021x4 supports dynamic voltage scaling to optimize its power consumption in Run mode. The voltage from the internal low-drop regulator that supplies the logic can be adjusted according to the system's maximum operating frequency and the external voltage supply.

There are three power consumption ranges:

- Range 1 (V_{DD} range limited to 1.71-3.6 V), with the CPU running at up to 32 MHz
- Range 2 (full V_{DD} range), with a maximum CPU frequency of 16 MHz
- Range 3 (full V_{DD} range), with a maximum CPU frequency limited to 4.2 MHz

Seven low-power modes are provided to achieve the best compromise between low-power consumption, short startup time and available wakeup sources:

Sleep mode

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs. Sleep mode power consumption at 16 MHz is about 1 mA with all peripherals off.

Low-power run mode

This mode is achieved with the multispeed internal (MSI) RC oscillator set to the low-speed clock (max 131 kHz), execution from SRAM or Flash memory, and internal regulator in low-power mode to minimize the regulator's operating current. In Low-power run mode, the clock frequency and the number of enabled peripherals are both limited.

Low-power sleep mode

This mode is achieved by entering Sleep mode with the internal voltage regulator in low-power mode to minimize the regulator's operating current. In Low-power sleep mode, both the clock frequency and the number of enabled peripherals are limited; a typical example would be to have a timer running at 32 kHz.

When wakeup is triggered by an event or an interrupt, the system reverts to the Run mode with the regulator on.

Stop mode with RTC

The Stop mode achieves the lowest power consumption while retaining the RAM and register contents and real time clock. All clocks in the V_{CORE} domain are stopped, the PLL, MSI RC, HSE and HSI RC oscillators are disabled. The LSE or LSI is still running. The voltage regulator is in the low-power mode.

Some peripherals featuring wakeup capability can enable the HSI RC during Stop mode to detect their wakeup condition.

The device can be woken up from Stop mode by any of the EXTI line, in $3.5 \mu s$, the processor can serve the interrupt or resume the code. The EXTI line source can be any GPIO. It can be the PVD output, the comparator 1 event or comparator 2 event



STM32L021x4 Functional overview

Five BOR thresholds are available through option bytes, starting from 1.8 V to 3 V. To reduce the power consumption in Stop mode, it is possible to automatically switch off the internal reference voltage (V_{REFINT}) in Stop mode. The device remains in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR} , without the need for any external reset circuit.

Note:

The start-up time at power-on is typically 3.3 ms when BOR is active at power-up, the start-up time at power-on can be decreased down to 1 ms typically for devices with BOR inactive at power-up.

The devices feature an embedded programmable voltage detector (PVD) that monitors the $V_{DD/VDDA}$ power supply and compares it to the V_{PVD} threshold. This PVD offers 7 different levels between 1.85 V and 3.05 V, chosen by software, with a step around 200 mV. An interrupt can be generated when $V_{DD/VDDA}$ drops below the V_{PVD} threshold and/or when $V_{DD/VDDA}$ is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

3.4.3 Voltage regulator

The regulator has three operation modes: main (MR), low power (LPR) and power down.

- MR is used in Run mode (nominal regulation)
- LPR is used in the Low-power run, Low-power sleep and Stop modes
- Power down is used in Standby mode. The regulator output is high impedance, the kernel circuitry is powered down, inducing zero consumption but the contents of the registers and RAM are lost except for the standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE crystal 32 KHz oscillator, RCC CSR).

3.4.4 Boot modes

At startup, BOOT0 pin and nBOOT0, nBOOT1 and nBOOT_SEL option bits are used to select one of three boot options:

- Boot from Flash memory
- Boot from System memory
- Boot from embedded RAM

The boot loader is located in System memory. It is used to reprogram the Flash memory by using SPI1 (PA4, PA7, PA13 and PA14 on TSSOP14 package or PA4, PA5, PA6 and PA7 on other packages) or USART2 (PA2, PA3 and PA9, PA10). See STM32™ microcontroller system memory boot mode AN2606 for details.

Functional overview STM32L021x4

3.6 Low-power real-time clock and backup registers

The real time clock (RTC) and the 5 backup registers are supplied in all modes including standby mode. The backup registers are five 32-bit registers used to store 20 bytes of user application data. They are not reset by a system reset, or when the device wakes up from Standby mode.

The RTC is an independent BCD timer/counter. Its main features are the following:

- Calendar with subsecond, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format
- Automatically correction for 28, 29 (leap year), 30, and 31 day of the month
- Two programmable alarms with wake up from Stop and Standby mode capability
- Periodic wakeup from Stop and Standby with programmable resolution and period
- On-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize it with a master clock.
- Reference clock detection: a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision.
- Digital calibration circuit with 1 ppm resolution, to compensate for quartz crystal inaccuracy
- 2 anti-tamper detection pins with programmable filter. The MCU can be woken up from Stop and Standby modes on tamper event detection.
- Timestamp feature which can be used to save the calendar content. This function can be triggered by an event on the timestamp pin, or by a tamper event. The MCU can be woken up from Stop and Standby modes on timestamp event detection.

The RTC clock sources can be:

- A 32.768 kHz external crystal
- A resonator or oscillator
- The internal low-power RC oscillator (typical frequency of 37 kHz)
- The high-speed external clock

3.7 General-purpose inputs/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions, and can be individually remapped using dedicated alternate function registers. All GPIOs are high current capable. Each GPIO output, speed can be slowed (40 MHz, 10 MHz, 2 MHz, 400 kHz). The alternate function configuration of I/Os can be locked if needed following a specific sequence in order to avoid spurious writing to the I/O registers. The I/O controller is connected to a dedicated IO bus with a toggling speed of up to 32 MHz.

The BOOT0 pin is shared with PB9 GPIO pin. This pin is an input-only pin. If nBOOT_SEL option bit is reset, sampling this pin on NRST rising edge gives the internal BOOT0 state. This pin then works as PB9 pin. The input voltage characteristics of this pin are specific for BOOT0 pin type (see *Table 49: I/O static characteristics*).

Extended interrupt/event controller (EXTI)

The extended interrupt/event controller consists of 26 edge detector lines used to generate interrupt/event requests. Each line can be individually configured to select the trigger event



STM32L021x4 Pin descriptions

Table 12. Pin definitions (continued)

	F	Pin nı	ımbe	r						Pin fur	nctions
TSSOP14	UFQFPN20	TSSOP20	UFQFPN28	LQFP32	UFQFPN32 ⁽¹⁾	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
14	17	20	22	24	24	PA14	I/O	FT	-	SWCLK, LPTIM1_OUT, I2C1_SMBA, USART2_TX, SPI1_MISO, LPUART1_TX, COMP2_OUT	-
-	-	-	23	25	25	PA15	I/O	FT	-	SPI1_NSS, TIM2_ETR, EVENTOUT, USART2_RX, TIM2_CH1	-
-	-	-	24	26	26	PB3	I/O	FT	-	SPI1_SCK, TIM2_CH2, EVENTOUT	COMP2_INM
-	-	-	25	27	27	PB4	I/O	FT	-	SPI1_MISO, EVENTOUT	COMP2_INP
-	-	-	26	28	28	PB5	I/O	FT	-	SPI1_MOSI, LPTIM1_IN1, I2C1_SMBA, TIM21_CH1	COMP2_INP
-	18	-	27	29	29	PB6	I/O	FTf	-	USART2_TX, I2C1_SCL, LPTIM1_ETR, TIM2_CH3, LPUART1_TX	COMP2_INP
-	19	1	28	30	30	PB7	I/O	FTf	-	USART2_RX, I2C1_SDA, LPTIM1_IN2, TIM2_CH4, LPUART1_RX	COMP2_INP, VREF_PVD_IN
1	20	1	1	31	31	PB9-BOOT0	I	В	-	-	BOOT0 (Boot memory selection)
-	-	-	-	-	32	PB8	I/O	FTf	-	USART2_TX, EVENTOUT, I2C1_SCL, SPI1_NSS	-

Pin descriptions STM32L021x4

Table 12. Pin definitions (continued)

	F	Pin nı	ımbe	r						Pin functions			
TSSOP14	UFQFPN20	TSSOP20	UFQFPN28	LQFP32	UFQFPN32 ⁽¹⁾	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions		
-	-	-	-	32	-	VSS	S		(4)	-	-		
-	-	-	-	1	1	VDD	S	-	(5)	-	-		

- 1. VSS pins are connected to the exposed pad (see Figure 35: UFQFPN32, 5 x 5 mm, 32-pin package outline).
- 2. Device reset input/internal reset output (active low).
- 3. Analog power supply.
- 4. On TSSOP14 package, $\rm V_{\rm DDA}$ is internally connected to $\rm V_{\rm DD}.$
- 5. Digital and analog ground.
- 6. Digital power supply.

6.3 Operating conditions

6.3.1 General operating conditions

Table 17. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit			
f _{HCLK}	Internal AHB clock frequency	-	0	32				
f _{PCLK1}	Internal APB1 clock frequency	-	0	32	MHz			
f _{PCLK2}	Internal APB2 clock frequency	-	0	32				
		BOR detector disabled	1.65	3.6				
V _{DD}	Standard operating voltage	BOR detector enabled, at power on	1.8	3.6	V			
		BOR detector disabled, after power on	1.65	3.6				
V _{DDA}	Analog operating voltage (all features)	Must be the same voltage as $V_{\mathrm{DD}}^{(1)}$	1.65	3.6	V			
	Input voltage on FT, FTf and RST pins ⁽²⁾	2.0 V ≤ V _{DD} ≤3.6 V	-0.3	5.5				
\ \ <u>\</u>	Imput voltage on F1, F11 and R31 pins	1.65 V ≤ V _{DD} ≤2.0 V	-0.3	5.2	V			
V _{IN}	Input voltage on BOOT0 pin	-	0	5.5	V			
	Input voltage on TC pin	-	-0.3	V _{DD} +0.3				
		LQFP32 package	-	333				
		UFQFPN32 package	-	513				
	Power dissipation at $T_A = 85$ °C (range 6)	UFQFPN28 package	-	206				
	Power dissipation at T_A = 85 °C (range 6) or T_A =105 °C (rage 7) $^{(3)}$	TSSOP20 package	-	270				
		UFQFPN20 package	-	196				
D		TSSOP14 package	-	210	mW			
P _D		LQFP32 package	-	83	IIIVV			
		UFQFPN32 package	-	128				
	Power dissipation at T _A = 125 °C (range	UFQFPN28 package	-	52	-			
	3) (3)	TSSOP20 package	-	67				
		UFQFPN20 package	-	49				
		TSSOP14 package	-	53				

Table 18. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
\/	Drown out road throshold 2	Falling edge	2.45	2.55	2.6	
VBOR3	Brown-out reset threshold 5	Rising edge	2.54	2.66	2.7	
\/	Prown out road throshold 4	Falling edge	2.68	2.8	2.85	
VBOR3Falling edgeVBOR3Brown-out reset threshold 3Falling edgeVBOR4Brown-out reset threshold 4Falling edgeVBOR4Programmable voltage detector threshold 0Falling edgeVBOR4PVD threshold 1Falling edgeVBOR5PVD threshold 1Falling edgeVBOR5PVD threshold 2Falling edgeVBOR5PVD threshold 3Falling edgeVBOR5PVD threshold 4Falling edgeVBOR5PVD threshold 4Falling edgeVBOR5PVD threshold 5Falling edgeVBOR5PVD threshold 6Falling edge	Rising edge	2.78	2.9	2.95		
V		Falling edge	1.8	1.85	1.88	
VPVD0	threshold 0	Rising edge	1.88	1.94	1.99	
V	DVD throshold 1	Falling edge	1.98	2.04	2.09	
VPVD1	1 VD tillesiloid 1	Rising edge	2.08	2.14	2.18	V
V	DVD throshold 2	Falling edge	2.20	2.24	2.28	
VPVD2	1 VD tilleshold 2	Rising edge	2.28	2.34	2.38	
V	DVD throshold 2	Falling edge	2.39	2.44	2.48	
VPVD3	PVD threshold 3	Rising edge	2.47	2.54	2.58	
\/	DVD throshold 4	Falling edge	2.57	2.64	2.69	
VPVD4	FVD tillesiloid 4	Rising edge	2.68	2.74	2.79	
\/	DVD throshold F	Falling edge	2.77	2.83	2.88	
V _{PVD5}	PVD tilleshold 5	Rising edge	2.87	2.94	2.99	
\/	DVD throshold 6	Falling edge	2.97	3.05	3.09	
VPVD6	PVD tilleshold 6	Rising edge	3.08	3.15	3.20	
		BOR0 threshold	-	40	-	
V_{hyst}	Hysteresis voltage	All BOR and PVD thresholds excepting BOR0	-	100	-	mV

^{1.} Guaranteed by characterization results, not tested in production.

^{2.} Valid for device version without BOR at power up. Please see option "D" in Ordering information scheme for more details.

Table 25. Current consumption in Sleep mode

Symbol	Parameter	Table 25. Current	litions	f _{HCLK}	Тур	Max ⁽¹⁾	Unit
			Range 3,	1 MHz	36.5	70	
			V _{CORE} =1.2 V,	2 MHz	58	95	
			VOS[1:0]=11	4 MHz	100	150	
		f _{HSE} = f _{HCLK} up to 16 MHz included,	Range 2,	4 MHz	125	170	
		$f_{HSE} = f_{HCLK}/2$	V _{CORE} =1.5 V,	8 MHz	230	300	
		above 16 MHz (PLL ON) ⁽²⁾	VOS[1:0]=10	16 MHz	450	540	
		(== 5,	Range 1,	8 MHz	275	350	
	Supply current in Sleep		V _{CORE} =1.8 V,	16 MHz	555	650	
	mode, Flash		VOS[1:0]=01	32 MHz	1350	1600	
	OFF		Range 3,	65 kHz	15.5	32	
		MSI clock	V _{CORE} =1.2 V, VOS[1:0]=11	524 kHz	26.5	55	
				4.2 MHz	115	160	
		HSI16 clock source (16 MHz)	Range 2, V _{CORE} =1.5 V, VOS[1:0]=10	16 MHz	585	670	
(01)			Range 1, V _{CORE} =1.8 V, VOS[1:0]=01	32 MHz	1500	1700	
I _{DD} (Sleep)		f _{HSE} = f _{HCLK} up to 16 MHz included,	Range 3,	1 MHz	49	88	μA
			V _{CORE} =1.2 V, VOS[1:0]=11	2 MHz	69	120	
				4 MHz	115	190	
			Range 2, CORE=1.5 V, VOS[1:0]=10	4 MHz	135	200	
		$f_{HSE} = f_{HCLK}/2$		8 MHz	240	340	
		above 16 MHz (PLL ON) ⁽²⁾		16 MHz	460	650	
			Range 1,	8 MHz	290	400	
	Supply current		V _{CORE} =1.8 V,	16 MHz	565	750	
	in Sleep mode, Flash		VOS[1:0]=01	32 MHz	1350	1900	
	ON		Range 3,	65 kHz	26.5	46	
		MSI clock	V _{CORE} =1.2 V,	524 kHz	38.5	70	-
			VOS[1:0]=11	4.2 MHz	125	190	
		HSI16 clock source (16 MHz)	Range 2, V _{CORE} =1.5 V, VOS[1:0]=10	16 MHz	600	760	
			Range 1, V _{CORE} =1.8 V, VOS[1:0]=01	32 MHz	1500	1850	

^{1.} Guaranteed by characterization results at 125 °C, not tested in production, unless otherwise specified.



^{2.} Oscillator bypassed (HSEBYP = 1 in RCC_CR register).

Table 26. Current consumption in Low-power Run mode

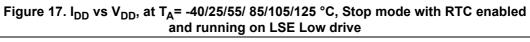
Symbol	Parameter		Conditions		Тур	Max ⁽¹⁾	Unit
				T _A = -40 °C to 25 °C	5.7	8.1	
			MSI clock, 65 kHz f _{HCLK} = 32 kHz	T _A = 85 °C	6.5	9	
				T _A = 105 °C	8	13	
		All		T _A = 125 °C	11.5	22	
		peripherals OFF, code		T _A =-40 °C to 25 °C	8.7	11	
		executed	MSI clock, 65 kHz	T _A = 85 °C	9.5	12	
		from RAM, Flash	f _{HCLK} = 65 kHz	T _A = 105 °C	11	15	
		switched		T _A = 125 °C	15	24	
		OFF, V _{DD} from 1.65 V		T _A = -40 °C to 25 °C	17	19	
	Supply current in Low-power	to 3.6 V	MSI clock, 131 kHz f _{HCLK} = 131 kHz	T _A = 55 °C	17	19.5	
				T _A = 85 °C	17.5	20	μΑ
				T _A = 105 °C	19	22	
I _{DD}				T _A = 125 °C	22.5	31	
(LP Run)			MSI clock, 65 kHz f _{HCLK} = 32 kHz	T _A = -40 °C to 25 °C	18	22	
	run mode			T _A = 85 °C	20	24	
				T _A = 105 °C	22	27	
				T _A = 125 °C	26.5	37	
		All peripherals		T _A = -40 °C to 25 °C	22	25	
		OFF, code	MSI clock, 65 kHz	T _A = 85 °C	24	27	
		executed from Flash,	f _{HCLK} = 65 kHz	T _A = 105 °C	26	30	
		V _{DD} from		T _A = 125 °C	30.5	39	
		1.65 V to 3.6 V		T _A = -40 °C to 25 °C	32	34	
				T _A = 55 °C	32.5	35	
			MSI clock, 131 kHz f _{HCLK} = 131 kHz	T _A = 85 °C	34	37	
			HOLK 1911	T _A = 105 °C	36	39	
				T _A = 125 °C	40	47	

^{1.} Guaranteed by characterization results at 125 $^{\circ}$ C, not tested in production, unless otherwise specified.

	Table 20. Typical and maximum carrent concampations in Ctop mode								
Symbol	Parameter	Conditions	Тур	Max ⁽¹⁾	Unit				
		$T_A = -40$ °C to 25°C	0.34	0.99					
	Supply current in Stop mode	T _A = 55°C	0.43	1.9	μΑ				
I _{DD} (Stop)		T _A = 85°C	0.94	4.2					
		T _A = 105°C	2.0	9					
		T _A = 125°C	4.9	19					

Table 28. Typical and maximum current consumptions in Stop mode

^{1.} Guaranteed by characterization results at 125 °C, not tested in production, unless otherwise specified.



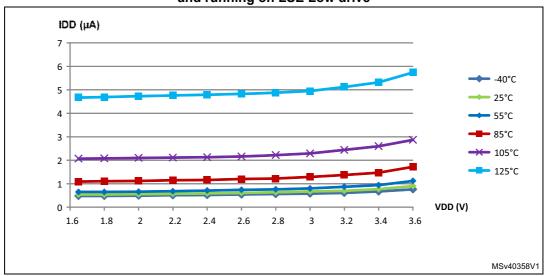
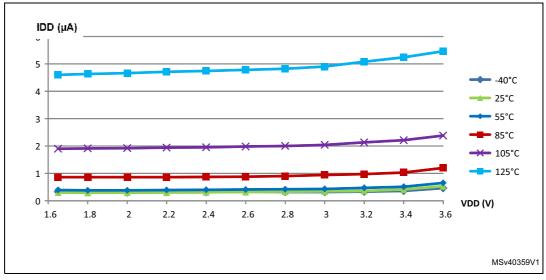


Figure 18. I_{DD} vs V_{DD} , at T_A = -40/25/55/85/105/125 °C, Stop mode with RTC disabled, all clocks OFF



6.3.7 Internal clock source characteristics

The parameters given in *Table 37* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 17*.

High-speed internal 16 MHz (HSI16) RC oscillator

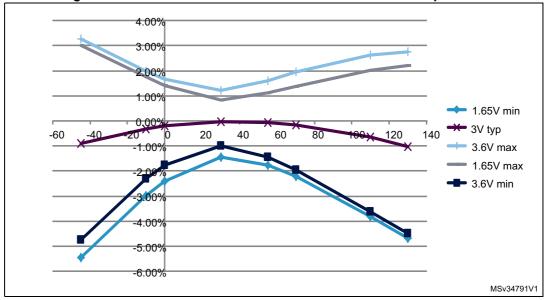
Table 37. 16 MHz HSI16 oscillator characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _{HSI16}	Frequency	V _{DD} = 3.0 V	-	16	-	MHz
TRIM ⁽¹⁾⁽²⁾	HSI16 user-	Trimming code is not a multiple of 16	-	±0.4	0.7	%
TRIM` '` '	trimmed resolution	Trimming code is a multiple of 16	- 16 - ot a multiple of 16 - ±0.4 0.7 multiple of 16 - ±1.5 25 °C -1 ⁽³⁾ - 1 ⁽³⁾ 0 to 55 °C -1.5 - 1.5 -10 to 70 °C -2 - 2 -10 to 85 °C -2.5 - 2 -10 to 105 °C -4 - 2	%		
		V _{DDA} = 3.0 V, T _A = 25 °C	-1 ⁽³⁾	-	1 ⁽³⁾	%
	Accuracy of the factory-calibrated HSI16 oscillator	V_{DDA} = 3.0 V, T_{A} = 0 to 55 °C	-1.5	-	1.5	%
۸۵۵		V_{DDA} = 3.0 V, T_A = -10 to 70 °C	-2	-	2	%
ACC _{HSI16}		V_{DDA} = 3.0 V, T_{A} = -10 to 85 °C	-2.5	-	2	%
		V_{DDA} = 3.0 V, T_{A} = -10 to 105 °C	-4	-	2	%
		V _{DDA} = 1.65 V to 3.6 V T _A = -40 to 125 °C	-5.45	-	3.25	%
t _{SU(HSI16)} ⁽²⁾	HSI16 oscillator startup time	-	-	3.7	6	μs
I _{DD(HSI16)} ⁽²⁾	HSI16 oscillator power consumption	-	-	100	140	μА

^{1.} The trimming step differs depending on the trimming code. It is usually negative on the codes which are multiples of 16 (0x00, 0x10, 0x20, 0x30...0xE0).

- 2. Guaranteed by characterization results, not tested in production.
- 3. Guaranteed by test in production.

Figure 22. HSI16 minimum and maximum value versus temperature



Low-speed internal (LSI) RC oscillator

Table 38. LSI oscillator characteristics

Symbol	Parameter	Min	Тур	Max	Unit
f _{LSI} ⁽¹⁾	LSI frequency	26	38	56	kHz
D _{LSI} ⁽²⁾	LSI oscillator frequency drift 0°C ≤ T _A ≤ 85°C	-10	-	4	%
t _{su(LSI)} ⁽³⁾	LSI oscillator startup time	-	-	200	μs
I _{DD(LSI)} ⁽³⁾	LSI oscillator power consumption	-	400	510	nA

- 1. Guaranteed by test in production.
- 2. This is a deviation for an individual part, once the initial frequency has been measured.
- 3. Guaranteed by design, not tested in production.

Multi-speed internal (MSI) RC oscillator

Table 39. MSI oscillator characteristics

Symbol	Parameter	Condition	Тур	Max	Unit		
		MSI range 0	65.5	-			
		MSI range 1	131	-	kHz		
		MSI range 2					
f _{MSI}	Frequency after factory calibration, done at V_{DD} = 3.3 V and T_A = 25 °C	MSI range 3	524	-			
	BB 3 3 4 A A	MSI range 4 1.05 - MSI range 5 2.1 - MH					
		MSI range 6	4.2	-			
ACC _{MSI}	Frequency error after factory calibration	-	±0.5	-	%		
D _{TEMP(MSI)} ⁽¹⁾	MSI oscillator frequency drift $0 \text{ °C} \le T_A \le 85 \text{ °C}$	-	±3	-	%		
D _{VOLT(MSI)} ⁽¹⁾	MSI oscillator frequency drift 1.65 V \leq V _{DD} \leq 3.6 V, T _A = 25 °C	-	-	2.5	%/V		
		MSI range 0	0.75	-			
		MSI range 1	1	-			
		MSI range 2	1.5	-			
I _{DD(MSI)} ⁽²⁾	MSI oscillator power consumption	MSI range 3	2.5	-	μA		
	MSI range 4 4.5			-			
		MSI range 5	8	-			
		MSI range 6	15	-			

Table 47. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T _A = +125 °C conforming to JESD78A	II level A

6.3.12 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of $-5 \mu A/+0 \mu A$ range), or other functional failure (for example reset occurrence oscillator frequency deviation).

The test results are given in the Table 48.

Table 48. I/O current injection susceptibility

		Functional susceptibil			
Symbol	Description	Negative injection	Positive injection	Unit	
	Injected current on BOOT0	-0	NA		
I _{INJ}	Injected current on all FT pins	-5 ⁽¹⁾	NA	mA	
	Injected current on any other pin	-5 ⁽¹⁾	+5		

It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

6.3.19 Communications interfaces

I²C interface characteristics

The I²C interface meets the timings requirements of the I²C-bus specification and user manual rev. 03 for:

- Standard-mode (Sm): with a bit rate up to 100 kbit/s
- Fast-mode (Fm): with a bit rate up to 400 kbit/s
- Fast-mode Plus (Fm+): with a bit rate up to 1 Mbit/s.

The I²C timing requirements are guaranteed by design when the I²C peripheral is properly configured (refer to the reference manual for details) and when the I2CCLK frequency is greater than the minimum given in *Table 62*. The SDA and SCL I/O requirements are met with the following restrictions: the SDA and SCL I/O pins are not "true" open-drain. When configured as open-drain, the PMOS connected between the I/O pin and VDDIOx is disabled, but is still present. Only FTf I/O pins support Fm+ low level output current maximum requirement (refer to *Section 6.3.13: I/O port characteristics* for the I2C I/Os characteristics).

All I²C SDA and SCL I/Os embed an analog filter (see *Table 61* for the analog filter characteristics).

Table 61. I2C analog filter characteristics⁽¹⁾

Symbol	Parameter	Min	Max	Unit
t _{AF}	Maximum pulse width of spikes that are suppressed by the analog filter	50 ⁽²⁾	100 ⁽³⁾	ns

- 1. Guaranteed by design, not tested in production.
- 2. Spikes with widths below $t_{AF(min)}$ are filtered.
- 3. Spikes with widths above $t_{\text{AF}(\text{max})}$ are not filtered

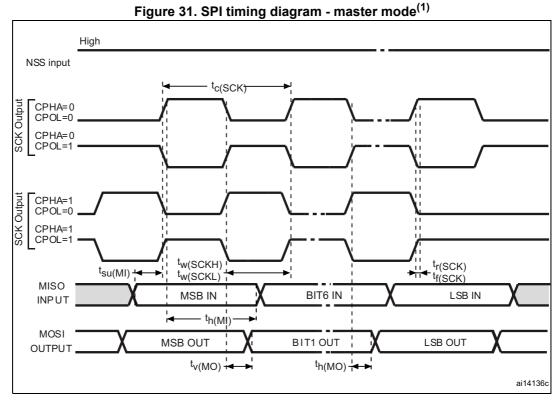
Table 62. I2C frequency in all I2C modes

Symbol	Parameter	Condition		Min	Unit
f _{12CCLK}		Standard-mode		2	
		Fast-mode			
	I2C clock frequency	Fast-mode Plus	Analog filter ON, DNF = 0	18	MHz
		rasi-mode Plus	Analog filter OFF, DNF = 1	16	

NSS input tsu(NSS) 🕌 tc(SCK) th(NSS) CPHA=1 CPOL=0 tw(SCKH) CPHA=1 CPOL=1 tw(SCKL) tr(SCK) th(SO) tv(SO) tdis(SO) ta(SO) tf(SCK) MISO MSB OUT **BIT6 OUT** LSB OUT OUTPUT th(SI) tsu(SI) MOSI MSB IN LSB IN BIT 1 IN **INPUT** ai14135b

Figure 30. SPI timing diagram - slave mode and CPHA = $1^{(1)}$

1. Measurement points are done at CMOS levels: $\rm 0.3V_{DD}$ and $\rm 0.7V_{DD.}$



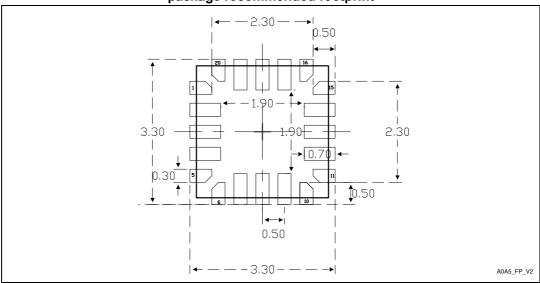
1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

Table 70. UFQFPN20 - 20-lead, 3x3 mm, 0.5 mm pitch, ultra thin fine pitch quad flat package mechanical data

Symbol		millimeters		inches ⁽¹⁾		
	Min	Тур	Max	Min	Тур	Max
Α	0.500	0.550	0.600	0.0197	0.0217	0.0236
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020
A3	-	0.152	-	-	0.060	-
D	-	3.000	-	-	0.1181	-
E	-	3.000	-	-	0.1181	-
L1	0.500	0.550	0.600	0.0197	0.0217	0.0236
L2	0.300	0.350	0.400	0.0118	0.0138	0.0157
L3	-	0.375	-	-	0.0148	-
L4	-	0.200	-	-	0.0079	-
L5	-	0.150	-	-	0.0059	-
b	0.180	0.250	0.300	0.0071	0.0098	0.0118
е	-	0.500	-	-	0.0197	-
ddd	-		0.050			0.0020

^{1.} Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 41. UFQFPN20 - 20-lead, 3x3 mm, 0.5 mm pitch, ultra thin fine pitch quad flat package recommended footprint



^{1.} Dimensions are expressed in millimeters.

STM32L021x4 Revision history

9 Revision history

Table 75. Document revision history

Date	Revision	Changes
07-Dec-2015	1	Initial release.
11-Feb-2016	2	Features: modified current consumption in run mode, Cortex®-M0+ core frequency range and total number of timers. Updated ADC conversion consumption on cover page. Updated ADC conversion consumption on cover page. Updated UFQFPN28 pinout: Figure 5: STM32L021x4 UFQFPN28 pinout and Table 12: Pin definitions. Updated Table 54: RAIN max for fADC = 16 MHz. Modified TS_CAL2 description in Table 56: Temperature sensor calibration values. Added Section: UFQFPN20 device marking, Section: TSSOP14 device marking and Section: UFQFPN28 device marking.
17-Mar-2016	3	Changed minimum comparator supply voltage to 1.65 V on cover page. Added baudrate allowing to wake up the MCU from Stop mode in Section 3.16.3: Low-power universal asynchronous receiver transmitter (LPUART). Added number of fast and standard channels in Section 3.10: Analog-to-digital converter (ADC). Updated Table 15: Current characteristics to add the total output current for STM32L021GxUx. Changed V _{DDA} minimum value to 1.65 V in Table 17: General operating conditions. Updated Table 25: Current consumption in Sleep mode, Table 26: Current consumption in Low-power Run mode, Table 27: Current consumption in Low-power Sleep mode and Table 29: Typical and maximum current consumptions in Standby mode. Section 6.3.15: 12-bit ADC characteristics: — Table 53: ADC characteristics: Distinction made between V _{DDA} for fast and standard channels; added note 1. Updated condition for f _{TRIG} measurement. Added note 4. related to R _{ADC} and removed measurement condition. Updated t _S and t _{CONV} . — Updated equation 1 description. — Updated Table 54: RAIN max for fADC = 16 MHz for f _{ADC} = 16 MHz and distinction made between fast and standard channels. — Updated measurement condition in Table 55: ADC accuracy. Added Table 63: USART/LPUART characteristics.